

Dual High-Voltage Schottky Rectifiers

Product Character	◆ Half Bridge Rectified、Common Cathode Structure. ◆ Multilayer Metal -Silicon Potential Structure. ◆ Low Power Waste, High Efficiency. ◆ Beautiful High Temperature Character. ◆ Have Over Voltage protect loop, high reliability. ◆ RoHs Product.
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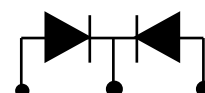
Typical Reference Data

VRRM= 100V
IF(AV)= 40A



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Polarity



Primary Use	● Low Voltage High Frequency Switching Power Supply. ● Low Voltage High Frequency Invers Circuit. ● Low Voltage Continued Circuit and Protection Circuit.
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Summarize	■ MBR40100 Schottky diode, in the manufacture uses the main process technology includes: Silicon epitaxial substrate, P+ loop technology, The potential metal and the silicon alloy technology, the device uses the two chip, the common cathode, the plastic half package structure.
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Absolute Maximum Ratings

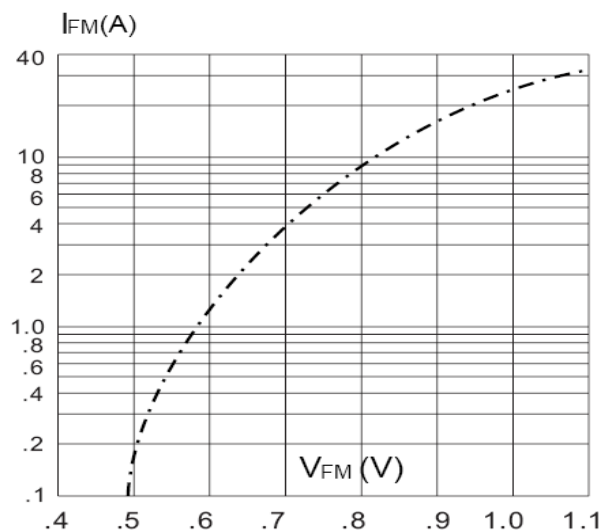
Item	Symbol	SS04C10E	Unit
Maximal Inverted Repetitive Peak Voltage	VRRM	100	V
Maximal DC Interdiction Voltage	VDC	100	V
Average Rectified Forward Current TC=150℃ Whole Device	IFAV	40	A
Unilateral		20	
Forward Peak Surge Current (Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	IFSM	300	A
Operating Junction Temperature	TJ	-40- +175	℃
Storage Temperature	TSTG	-40- +175	℃
Maximum Thermal Resistance Junction-to-Case	RθJC	2.0	℃/W

Electricity Character

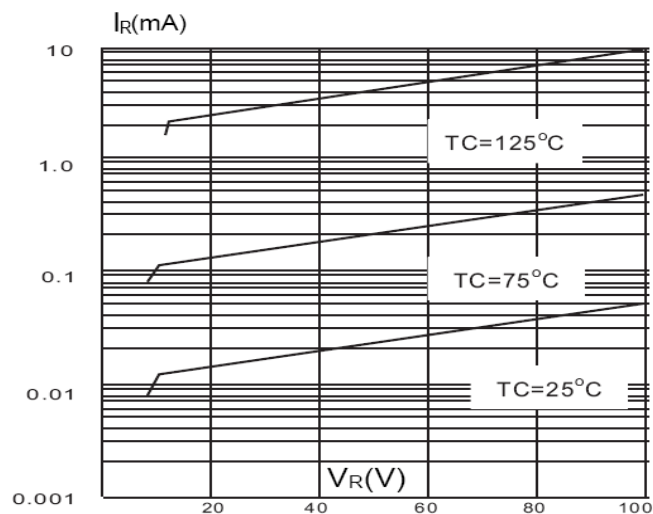
Item	Test Condition		Minimum	Representative	Maximum	Unit
IR	TJ =25℃	VR=VRRM			100	uA
	TJ =125℃				1	mA
VF	TJ =25℃	IF=20A			0.88	V

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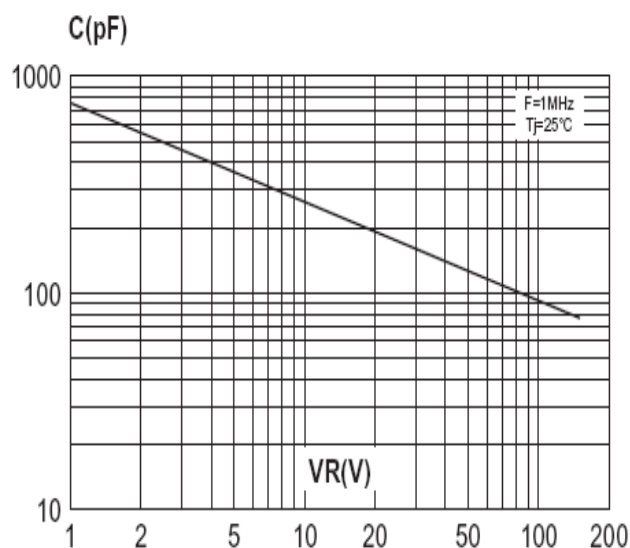
The forward voltage and forward current curve



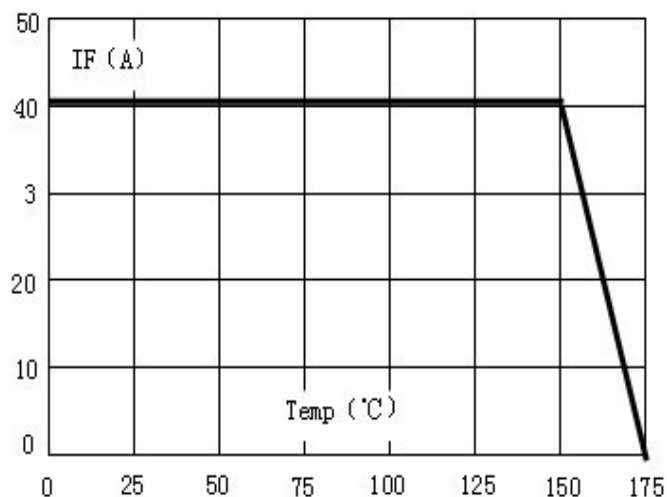
The reverse leak current and the reverse voltage (single-device) curve



The crunode capacitance curve



Current Derating Curve, Per Element



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T0-220AB

